

### KSC5039

# **High Voltage Power Switch Switching Application**



1.Base 2.Collector 3.Emitter

### **NPN Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	800	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	5	Α
I <sub>CP</sub>	Collector Current (Pulse)	10	Α
I <sub>B</sub>	Base Current	3	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	70	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

### **Electrical Characteristics** $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	800			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	400			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_C = 1mA$ , $I_C=0$	7			
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 500 \text{ V}, I_{E} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 7V, I_{C} = 0$			10	μΑ
h <sub>FE</sub>	* DC Current Gain	$V_{CE} = 5V, I_{C} = 0.3A$	10			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = 2.5A, I_B = 0.5A$			1.5	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	$I_C = 2.5A, I_B = 0.5A$			2.0	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 5V, I_{C} = 0.1A$		10		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V , f = 1MHz		40		pF
t <sub>ON</sub>	Turn ON Time	$V_{CC} = 150V, I_{C} = 2.5A$			1	μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = 0.5A$			3	μs
t <sub>F</sub>	Fall Time	$R_L = 60\Omega$			0.8	μs

<sup>\*</sup> Plus test: PW=300µs, Duty Cycle=2% Pulsed

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# **Typical Characteristics**

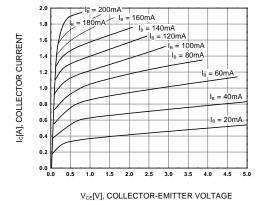


Figure 1. Static Characteristic

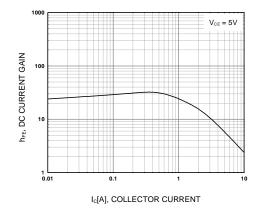


Figure 2. DC current Gain

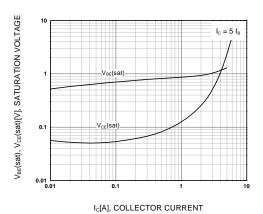


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

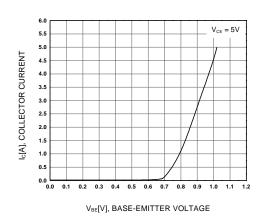


Figure 4. Base-Emitte On Voltage

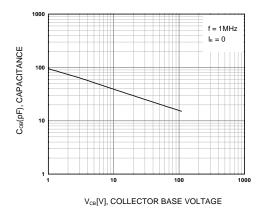


Figure 5. Collector Output Capacitance

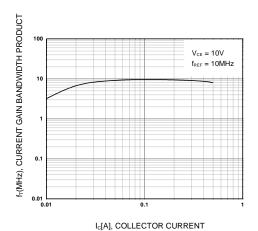


Figure 6. Current Gain Bandwidth Product

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# Typical Characteristics (Continued)

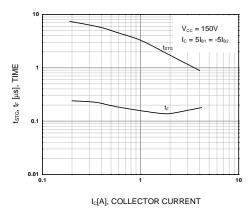


Figure 7. Switching Time

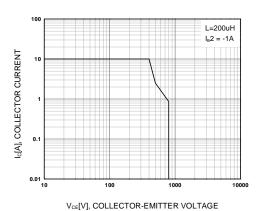


Figure 9. Reverse Bias Safe Operaing Area

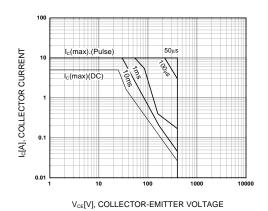


Figure 8. Safe Operating Area

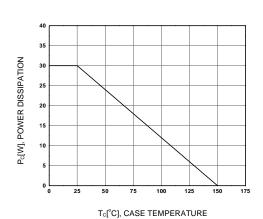
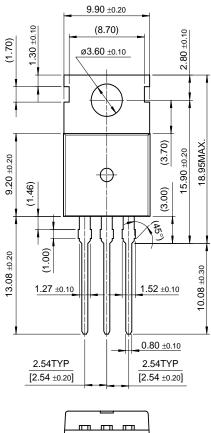


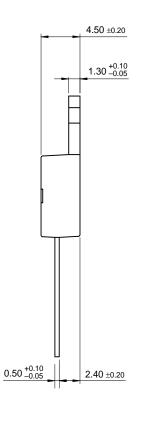
Figure 10. Power Derating

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# **Package Demensions**

# TO-220





10.00 ±0.20

Dimensions in Millimeters

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